

SE3090K

N-Channel Enhancement-Mode MOSFET

Revision: A

General Description

This type used advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of application

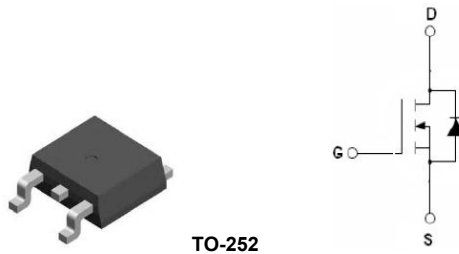
Features

For a single MOSFET

- $V_{DS} = 30V$
- $R_{DS(ON)} = 4.1m\Omega @ V_{GS}=10V$

Pin configurations

See Diagram below



Absolute Maximum Ratings

Parameter		Symbol	Rating	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	V
Drain Current	Continuous	I_D	90	A
	Pulsed		200	
Total Power Dissipation	@TA=25°C	P_D	105	W
Derating factor			0.7	W/°C
Single pulse avalanche energy		E_{AS}	380	mJ
Operating Junction Temperature Range		T_J	-55 to 175	°C

Thermal Resistance

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance Junction to Case	-	1.43	°C/W

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Electrical Characteristics (T _J =25°C unless otherwise noted)						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS (Note 2)						
BV _{DSS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0 V	30	38		V
I _{DSS}	Drain to Source Leakage Current	V _{DS} = 30V, V _{GS} =0V			1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =20V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D =250μA	1	1.7	2.5	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =20A	-	4.1	5.8	mΩ
		V _{GS} =4.5V, I _D =20A	-	5.9	8	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =20A	20			S
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		3433		pF
C _{oss}	Output Capacitance			360		pF
C _{rss}	Reverse Transfer Capacitance			287		pF
SWITCHING PARAMETERS						
Q _g	Total Gate Charge ²	V _{GS} =10V, V _{DS} =15V, I _D =45A		60		nC
Q _{gs}	Gate Source Charge			8.2		nC
Q _{gd}	Gate Drain Charge			16.4		nC
t _{d(on)}	Turn-On Delay Time	V _{GS} =10V, V _{DS} =15V, R _{GEN} =3Ω I _D =20A		12		ns
t _{d(off)}	Turn-Off Delay Time			40		ns
t _{d(r)}	Turn-On Rise Time			15		ns
t _{d(f)}	Turn-Off Fall Time			14		ns
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =24A			1.2	V
I _S	Diode Forward Current				90	A
t _{rr}	Reverse Recovery Time	T _J =25°C, I _F =20A		29		nS
Q _{rr}	Reverse Recovery Charge	Di/dt=100A/μs		32		nC

Typical Characteristics

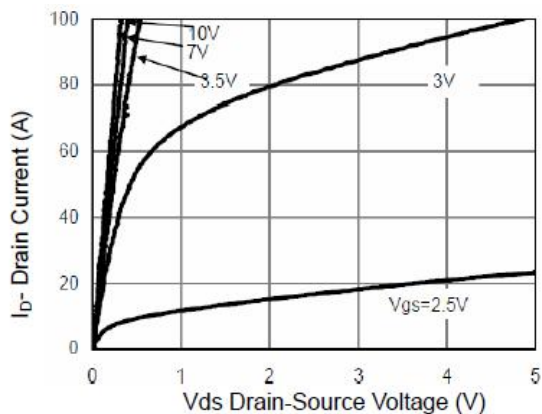


Figure 1 Output Characteristics

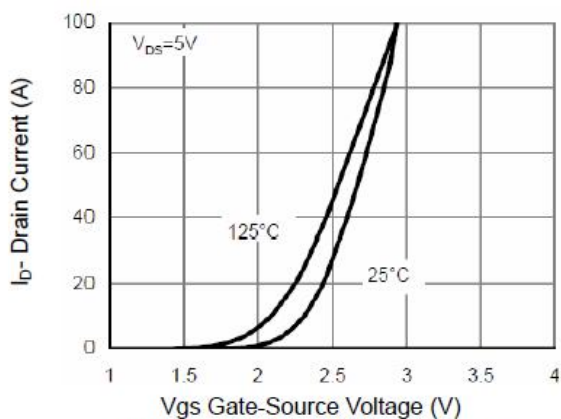


Figure 2 Transfer Characteristics

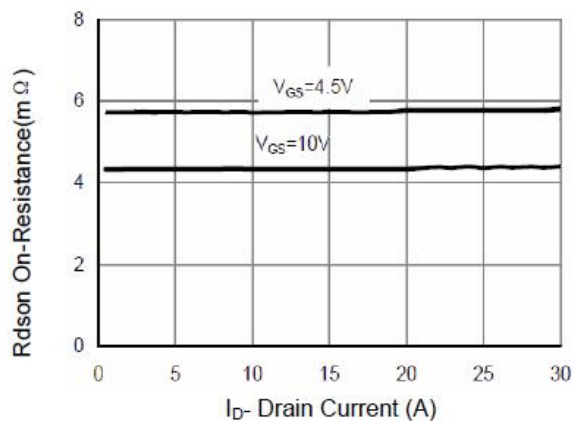


Figure 3 Rdson- Drain Current

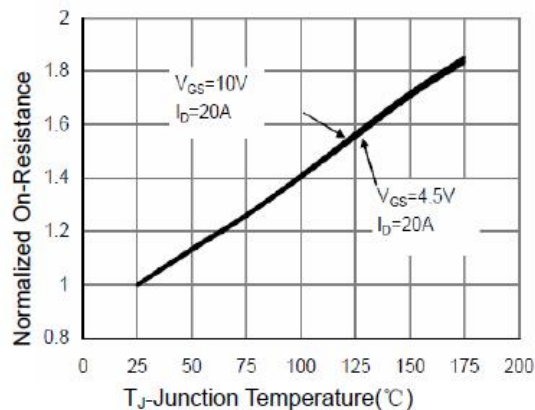


Figure 4 Rdson-Junction Temperature

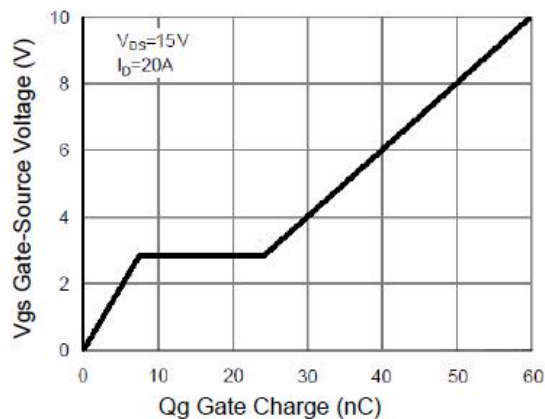


Figure 5 Gate Charge

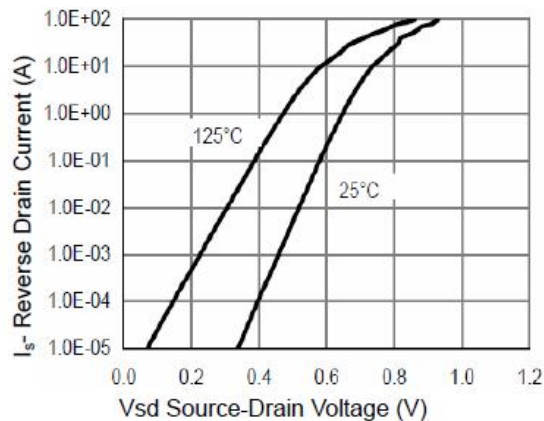


Figure 6 Source- Drain Diode Forward

Typical Characteristics

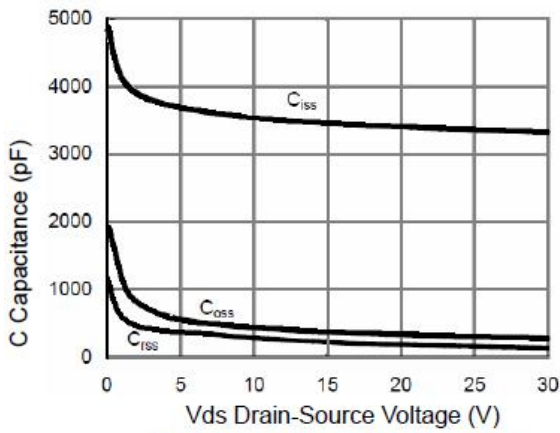


Figure 7 Capacitance vs Vds

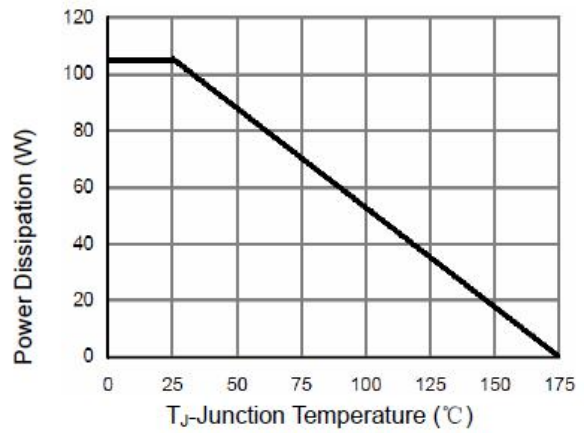


Figure 9 Power De-rating

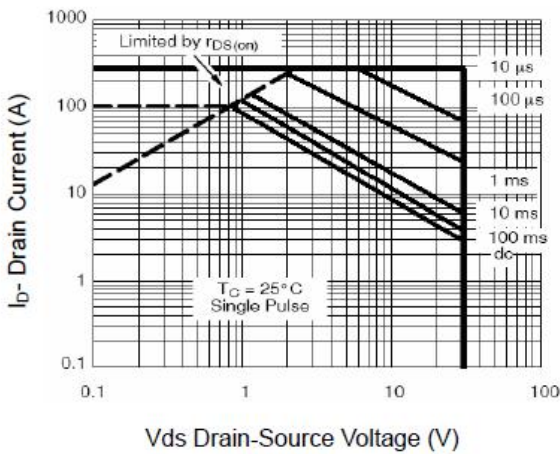


Figure 8 Safe Operation Area

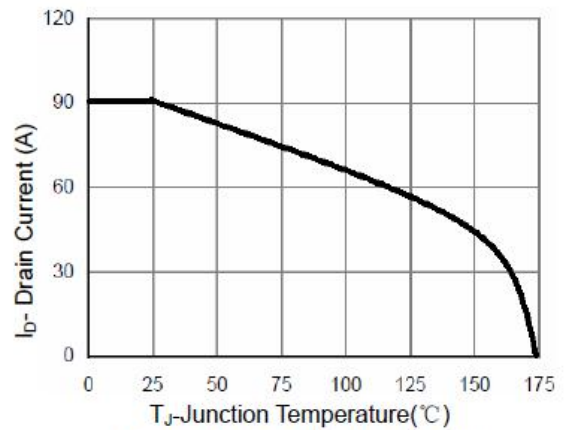


Figure 10 ID Current Derating

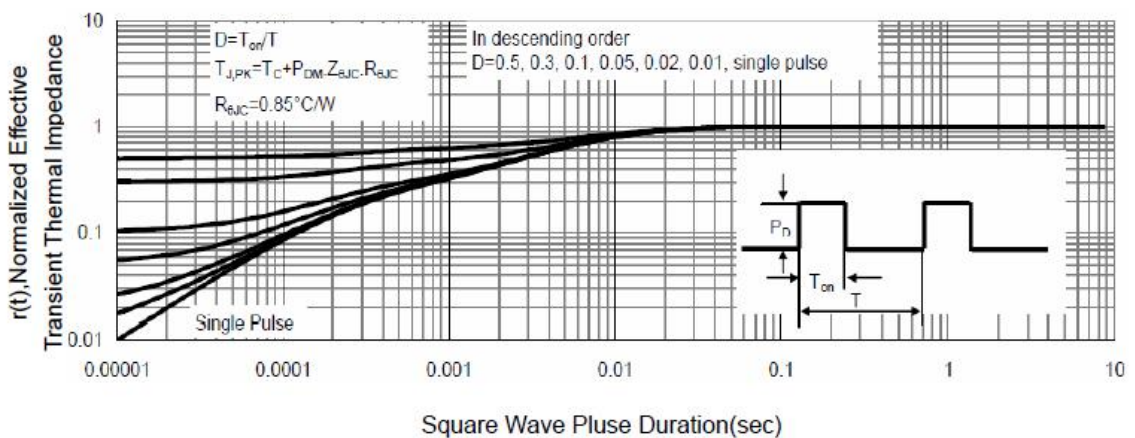
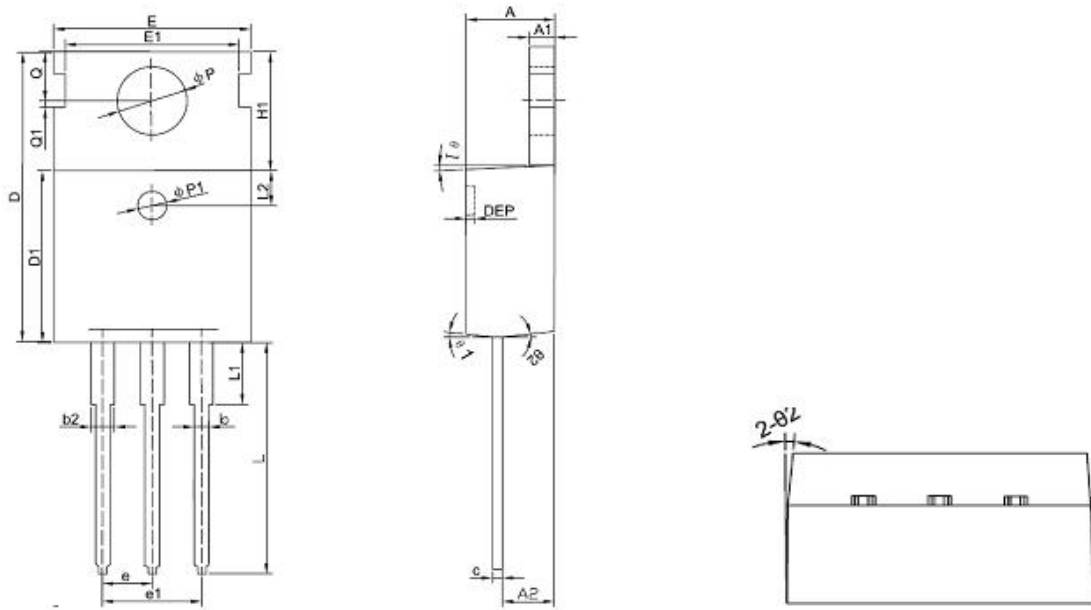


Figure 11 Normalized Maximum Transient Thermal Impedance

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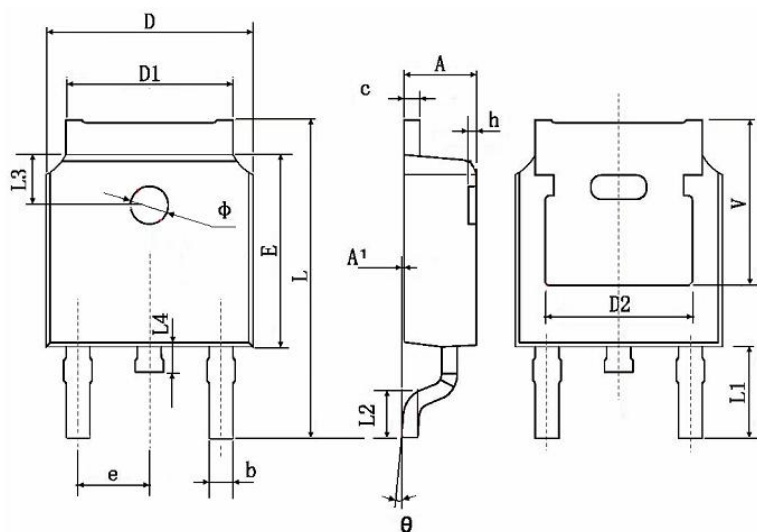
Package Outline Dimension

TO-220



Symbol	Dimension In Millimeters			Dimension In Inches		
	Min	Nom	Max	Min	Nom	Max
A	4.400	4.550	4.700	0.173	0.179	0.185
A1	1.270	1.300	1.330	0.050	0.051	0.052
A2	2.590	2.690	2.790	0.102	0.106	0.110
b	0.770	-	0.900	0.030	-	0.035
b2	1.230	-	1.360	0.048	-	0.054
c	0.480	0.500	0.520	0.019	0.020	0.020
D	15.100	15.400	15.700	-	0.606	-
D1	9.000	9.100	9.200	0.354	0.358	0.362
DEP	0.050	0.285	0.520	0.002	0.011	0.020
E	10.060	10.160	10.260	0.396	0.400	0.404
E1	-	8.700	-	-	0.343	-
ΦP1	1.400	1.500	1.600	0.055	0.059	0.063
e	2.54BSC			0.1BSC		
e1	5.08BSC			0.2BSC		
H1	6.100	6.300	6.500	0.240	0.248	0.256
L	12.750	12.960	13.170	0.502	0.510	0.519
L1	-	-	3.950	-	-	0.156
L2	1.85REF			0.073REF		
ΦP	3.570	3.600	3.630	0.141	0.142	0.143
Q	2.730	2.800	2.870	0.107	0.110	0.113
Q1	-	0.200	-	-	0.008	-
Θ1	5°	7°	9°	5°	7°	9°
Θ2	1°	3°	5°	1°	3°	5°

TO-252



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	0.483 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	

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